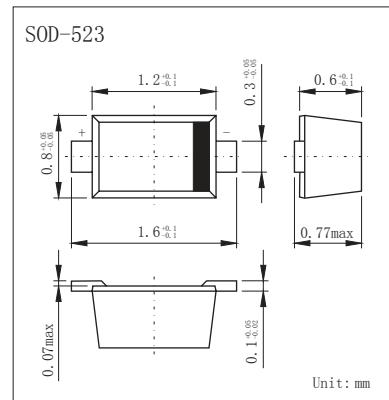
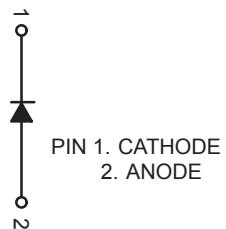


Schottky Diodes

RB751S-100(KB751S-100)

■ Features

- Extremely High Switching Speed
- Low-Forward Voltage and Low Reverse Current
- High Reliability
- Schottky Barrier Diodes Encapsulated in a SOD523 Package



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Peak Reverse voltage	V _{RM}	100	V
Average Rectified Output Current	I _o	200	mA
Junction Temperature	T _J	125	°C
Storage temperature range	T _{stg}	-40 to 150	

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	V _R	I _R = 100 uA	100			V
Forward voltage	V _{F1}	I _F = 200 mA			0.92	
Reverse voltage leakage current	I _{R1}	V _R =100 V			20	uA

■ Marking

NO.	RB751S-100
Marking	6